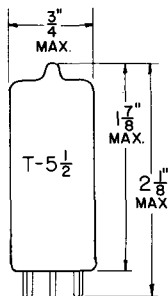


TUNG-SOL

PENTODE

MINIATURE TYPE



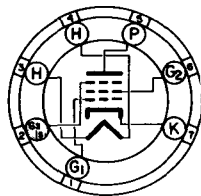
GLASS BULB

COATED UNIPOTENTIAL CATHODE

HEATER

18 VOLTS 0.10 AMP.

ANY MOUNTING POSITION



BOTTOM VIEW

MINIATURE BUTTON
7 PIN BASE

78K

THE 18GD6 IS A SHARP-CUTOFF PENTODE IN THE 7 PIN MINIATURE CONSTRUCTION. IT FEATURES A 100MILLIAMPERE HEATER AND IS DESIGNED FOR RF AND IF APPLICATIONS IN AC/DC TYPE RADIO RECEIVERS.

DIRECT INTERELECTRODE CAPACITANCES^A

GRID #1 TO PLATE (MAX.)	.0035	μf
INPUT: G1 TO (H+K+G2+G3+I.S.)	6.0	μf
OUTPUT: P TO (H+K+G2+G3+I.S.)	5.0	μf

RATINGS

INTERPRETED ACCORDING TO DESIGN MAXIMUM SYSTEM ^B

HEATER VOLTAGE	18	VOLTS
MAXIMUM PLATE VOLTAGE	150	VOLTS
MAXIMUM GRID #2 SUPPLY VOLTAGE	150	VOLTS
MAXIMUM GRID #2 VOLTAGE	SEE RATING CHART	
MAXIMUM PLATE DISSIPATION	2.5	WATTS
MAXIMUM GRID #2 DISSIPATION	0.6	WATTS
MAXIMUM HEATER-CATHODE VOLTAGE ^B	100	VOLTS

^A EXTERNAL SHIELD #316 CONNECTED TO PIN 7 (CATHODE)^B

DESIGN-MAXIMUM RATINGS ARE LIMITING VALUES OF OPERATING AND ENVIRONMENTAL CONDITIONS APPLICABLE TO A BOGEY ELECTRON DEVICE OF A SPECIFIED TYPE AS DEFINED BY ITS PUBLISHED DATA, AND SHOULD NOT BE EXCEEDED UNDER THE WORST PROBABLE CONDITIONS. THE DEVICE MANUFACTURER CHOOSES THESE VALUES TO PROVIDE ACCEPTABLE SERVICEABILITY OF THE DEVICE, TAKING RESPONSIBILITY FOR THE EFFECTS OF CHANGES IN OPERATING CONDITIONS DUE TO VARIATIONS IN DEVICE CHARACTERISTICS. THE EQUIPMENT MANUFACTURER SHOULD DESIGN SO THAT INITIALLY AND THROUGHOUT LIFE NO DESIGN-MAXIMUM VALUE FOR THE INTENDED SERVICE IS EXCEEDED WITH A BOGEY DEVICE UNDER THE WORST PROBABLE OPERATING CONDITIONS WITH RESPECT TO SUPPLY-VOLTAGE VARIATION, EQUIPMENT COMPONENT VARIATION, EQUIPMENT CONTROL ADJUSTMENT, LOAD VARIATION, SIGNAL VARIATION, AND ENVIRONMENTAL CONDITIONS.

TUNG-SOL

CONTINUED FROM PRECEDING PAGE

TYPICAL OPERATING CONDITIONS AND CHARACTERISTICS

HEATER VOLTAGE	18	VOLTS
HEATER CURRENT	0.10	AMP.
PLATE VOLTAGE	100	VOLTS
GRID #3 VOLTAGE	CONNECTED TO CATHODE AT SOCKET	100
GRID #2 VOLTAGE		
CATHODE BIAS RESISTOR	150	OHMS
PLATE CURRENT	5	MA.
GRID #2 CURRENT	2.0	MA.
TRANSCONDUCTANCE	4300	μ MHOS
PLATE RESISTANCE (APPROX.)	0.5	MEGOHM
EC1 FOR $I_b = 10 \mu A$ (APPROX.)	-4.7	VOLTS